

Phototransistor chip FT050

Description

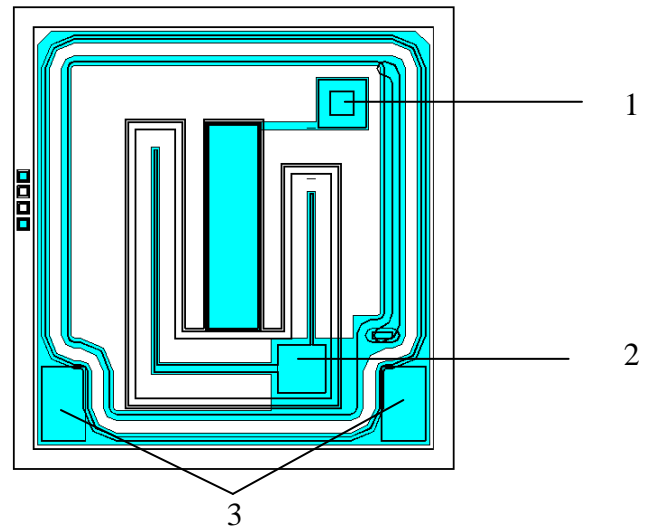
FT050 chip is fabricated using Silicon Bipolar process technology. This chip is designed to be used in optocouplers.

Features

- High Collector-Emitter Breakdown Voltage
- Chip size - 1.1 x 1.15 mm
- Chip thickness - 0.36 mm±0.02mm
- Contact pads size:
Base - 0.12 mm x 0.12 mm
Emitter - 0.12 mm x 0.12 mm
Collector - 0.11 mm x 0.185 mm
- Metallization: top - AlSi;
bottom (Collector) - CrNi for bonding on conductive adhesive

Absolute maximum ratings

Operating junction temperature	-45°C to 70°C
Limiting temperature	-60°C to 85°C



- 1 - Base
- 2 - Emitter
- 3 - Collector

Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min	Typ	Max	Unit	Conditions
Collector-Emitter Breakdown Voltage	BV_{CE}	220	-	-	V	$I_{CE}=10\text{ mA}$
Collector-Emitter Leakage Current	$I_{LEAK\ CE}$	-	-	1.0	μA	$V_{CE}=250\text{ V}$
Collector-Emitter Saturation Voltage	$V_{CE\ SAT}$	-	-	0.4	V	$I_C=2\text{ mA}, I_B=150\ \mu\text{A}$
Current Transfer Ratio	h_{21E}	60	-	170	-	$V_{CE}=5\text{ V}, I_B=150\ \mu\text{A}$